

N-Channel Enhancement Mode Power MOSFET

Description

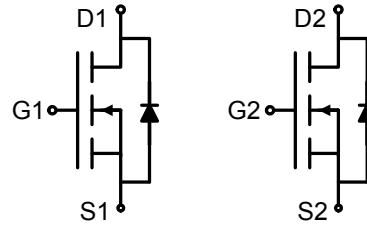
The TF3622 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other switching application.

General Feature

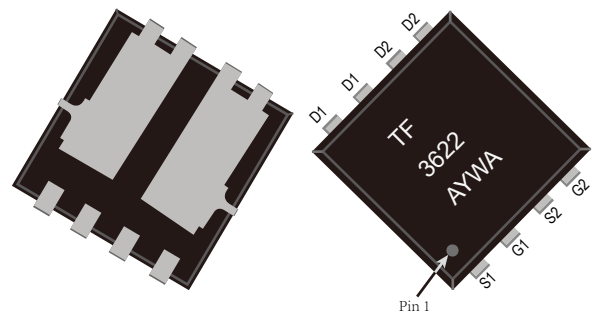
- $V_{DS} = 30V, I_D = 25A$
 $R_{DS(ON) Typ} = 10m\Omega @ V_{GS} = 10V$
 $R_{DS(ON) Typ} = 15m\Omega @ V_{GS} = 4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Battery switch
- DC/DC converter



Schematic diagram



PDFN3333-8 top view

Package Marking and Ordering Information:

Part NO.	TF3622
Marking1	TF:tuofeng; 3622: TF3622
Marking2	Y:year code; X:week code; AA:device code;
Basic ordering unit (pcs)	5000

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	25	A
Drain Current-Pulsed (Note 1)	I_{DM}	75	A
Maximum Power Dissipation	P_D	3.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

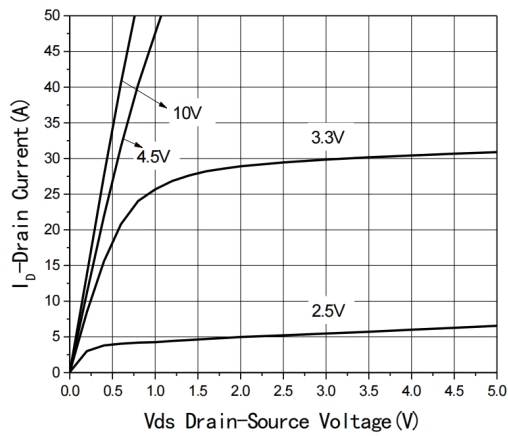
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	35	$^\circ C/W$
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

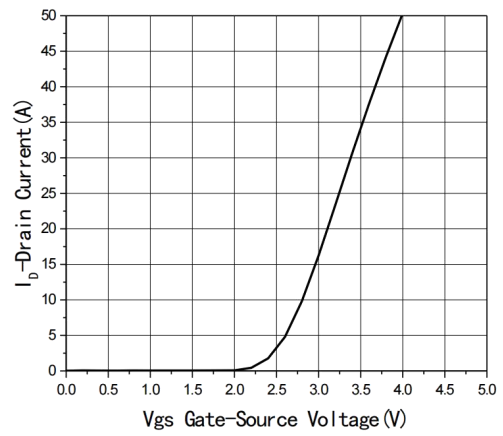
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =15A		10	13	m Ω
		V _{GS} =4.5V, I _D =10A		15	18	m Ω
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	1021	-	PF
Output Capacitance	C _{OSS}		-	273	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	166	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =1.5A V _{GS} =10V, R _{GEN} =1Ω	-	4.4	-	nS
Turn-on Rise Time	t _r		-	9	-	nS
Turn-Off Delay Time	t _{d(off)}		-	17	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =15A, V _{GS} =10V	-	19.5	-	nC
Gate-Source Charge	Q _{gs}		-	2.45	-	nC
Gate-Drain Charge	Q _{gd}		-	3.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =15A			1.2	V
Diode Forward Current ^(Note 2)	I _S				25	A

Notes:

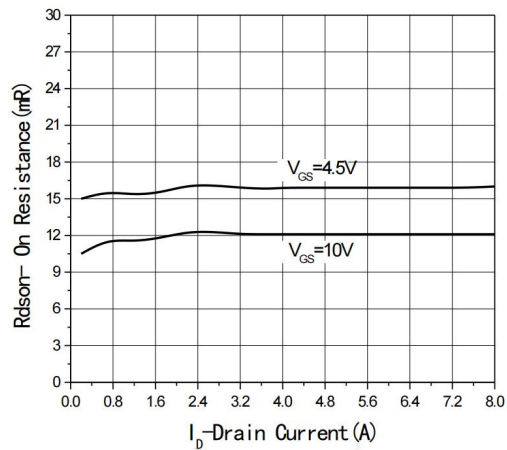
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production



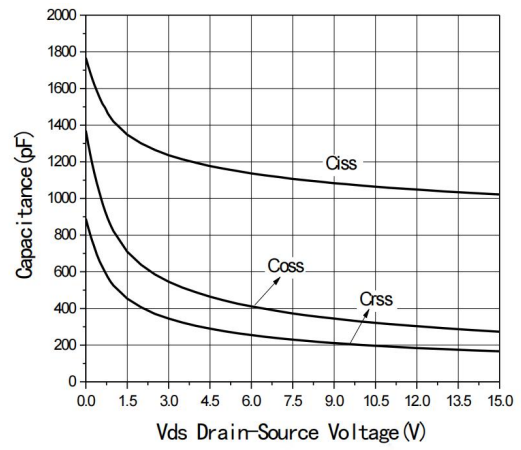
Output Characteristics



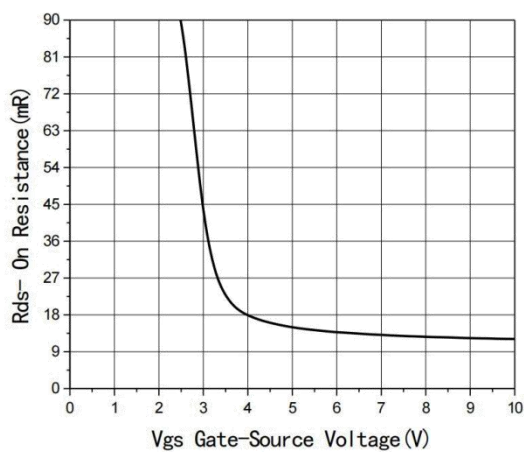
Typical Transfer Characteristics



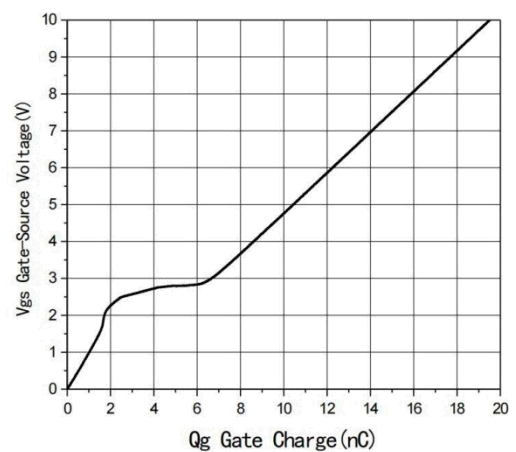
Rdson-Drain current



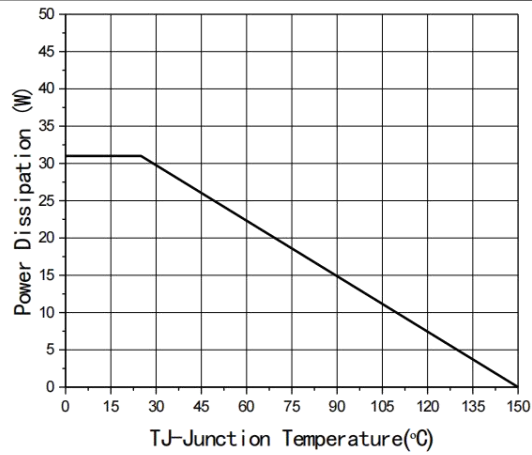
Capacitance vs Vds



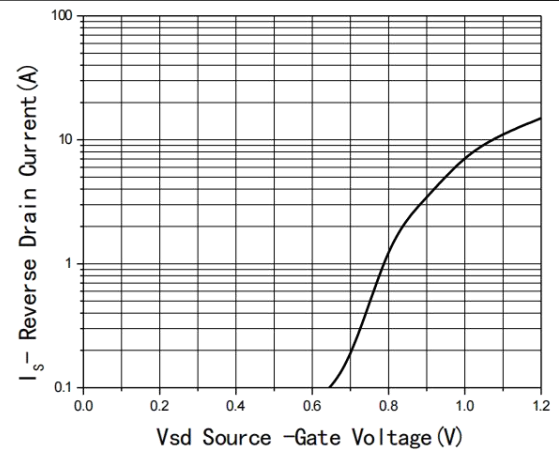
Rdson-Gate Drain voltage



Gate Charge

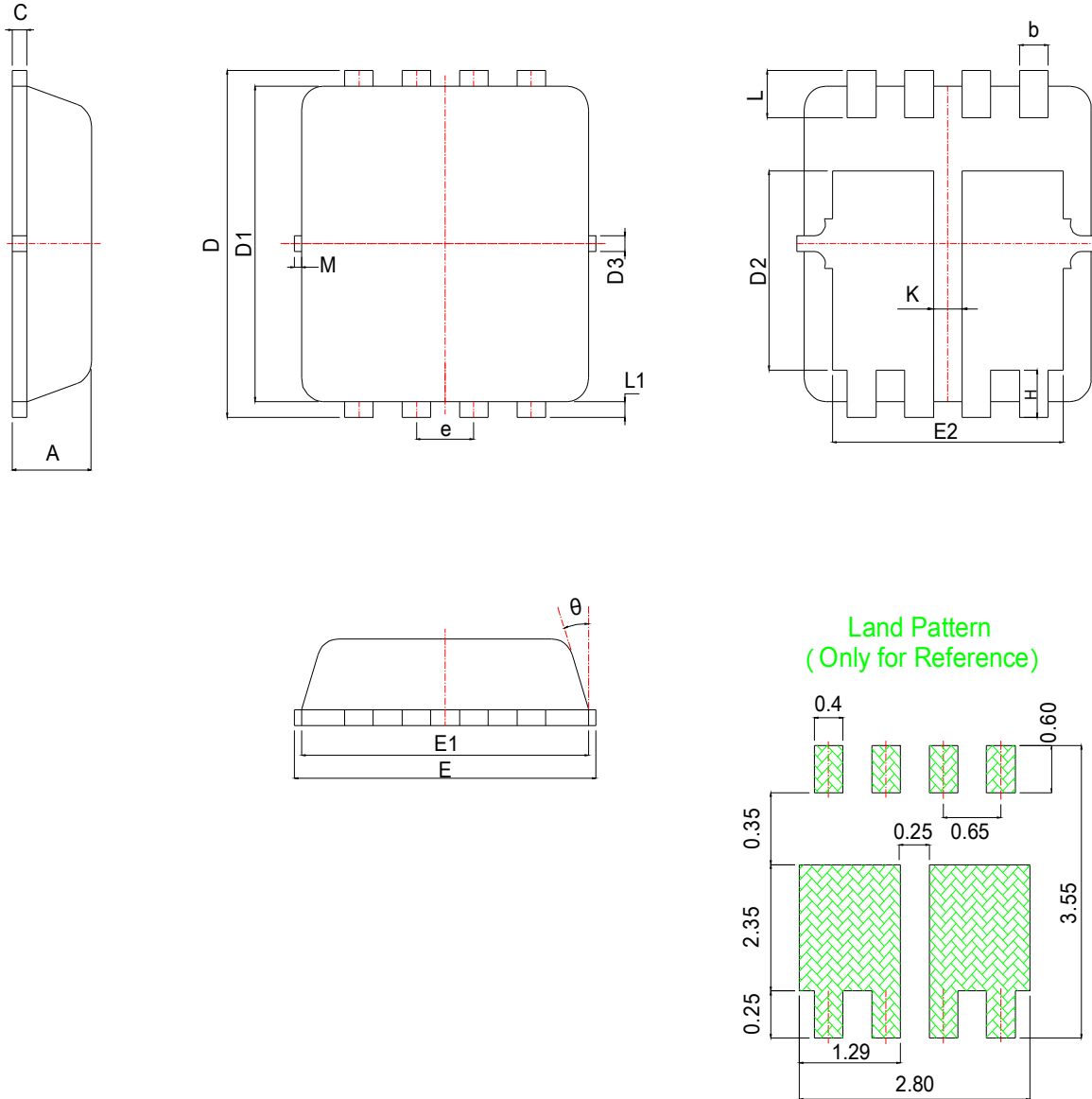


Power De-rating



Source-Drain Diode Forward

PDFN3333



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031	E1	3.00	3.15	3.20	0.118	0.122	0.126
b	0.25	0.30	0.35	0.010	0.012	0.014	E2	2.39	2.49	2.59	0.094	0.098	0.102
c	0.10	0.15	0.25	0.004	0.007	0.010	e	0.65BSC			0.026BSC		
D	3.25	3.35	3.45	0.128	0.132	0.136	H	0.30	0.40	0.50	0.012	0.016	0.020
D1	3.00	3.10	3.20	0.118	0.122	0.126	L	0.30	0.40	0.50	0.012	0.016	0.020
D2	1.78	1.88	1.98	0.070	0.074	0.078	L1	*	0.13	*	*	0.005	*
D3	*	0.13	*	*	0.005	*	theta	*	10°	12°	*	10°	12°
E	3.20	3.30	3.40	0.126	0.130	0.134	M	*	*	0.15	*	*	0.006
K	0.30	*	*	0.012	*	*							